International
IOR Rectifier

PD - 93854A

IRL1404S
IRL1404L

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

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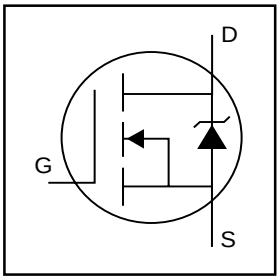


V_{DSS} = 40V

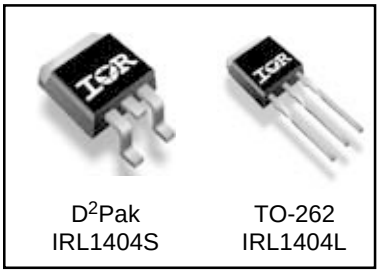
$R_{DS(on)}$ = 0.004Ω

I_D = 160A⑥

Description

Seventh Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.
The through-hole version (IRL1404L) is available for low-profile applications.



D²Pak IRL1404S | TO-262 IRL1404L

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	160⑥	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	110⑥	
I_{DM}	Pulsed Drain Current ①	640	
P_D @T_A = 25°C	Power Dissipation	3.8	W
P_D @T_C = 25°C	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	520	mJ
I_{AR}	Avalanche Current①	95	A
E_{AR}	Repetitive Avalanche Energy①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted)⑦	—	40	

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.038	—	V/°C	Reference to 25°C, $_D$ = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.004	Ω	V_{GS} = 10V, I_D = 95A ④
				0.0059		V_{GS} = 4.3V, I_D = 40A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	93	—	—	S	V_{DS} = 25V, I_D = 95A
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	µA	V_{DS} = 40V, V_{GS} = 0V
		—	—	250		V_{DS} = 32V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-200		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	140	nC	I_D = 95A
Q_{gs}	Gate-to-Source Charge	—	—	48		V_{DS} = 32V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	60		V_{GS} = 5.0V, See Fig. 6 ④
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	V_{DD} = 20V
t_r	Rise Time	—	270	—		I_D = 95A
$t_{d(off)}$	Turn-Off Delay Time	—	38	—		R_G = 2.5Ω V_{GS} = 4.5V
t_f	Fall Time	—	130	—		R_D = 0.25Ω ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	6600	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	1700	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	350	—		f = 1.0MHz, See Fig. 5
C_{oss}	Output Capacitance	—	6700	—		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	—	1500	—		V_{GS} = 0V, V_{DS} = 32V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance ⑤	—	1500	—		V_{GS} = 0V, V_{DS} = 0V to 32V

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	160⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	640		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 95A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	63	94	ns	T_J = 25°C, I_F = 95A
Q_{rr}	Reverse RecoveryCharge	—	170	250	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

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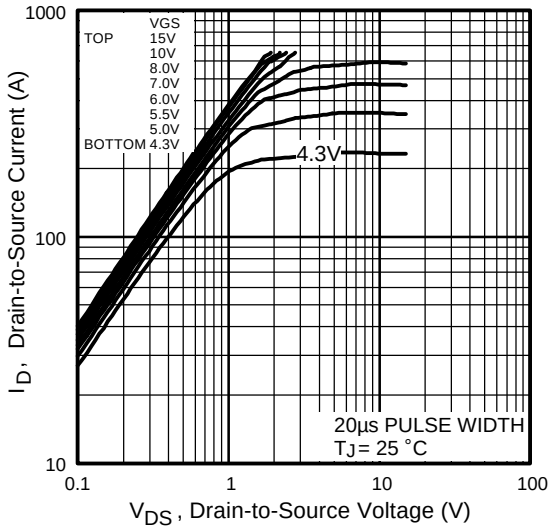

Fig 1. Typical Output Characteristics

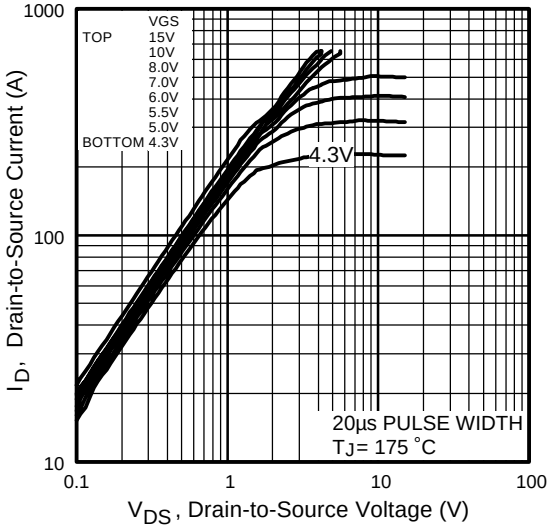

Fig 2. Typical Output Characteristics

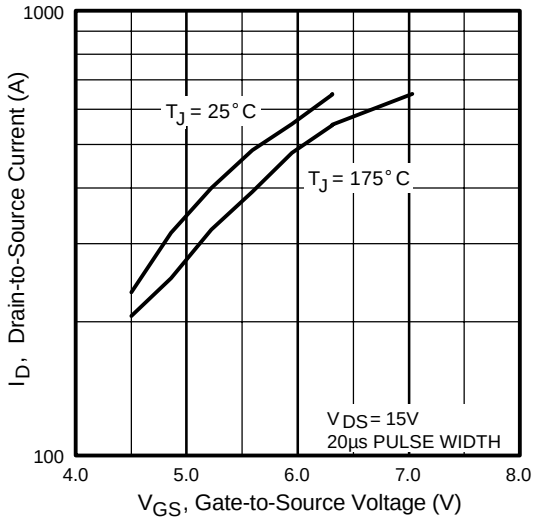

Fig 3. Typical Transfer Characteristics

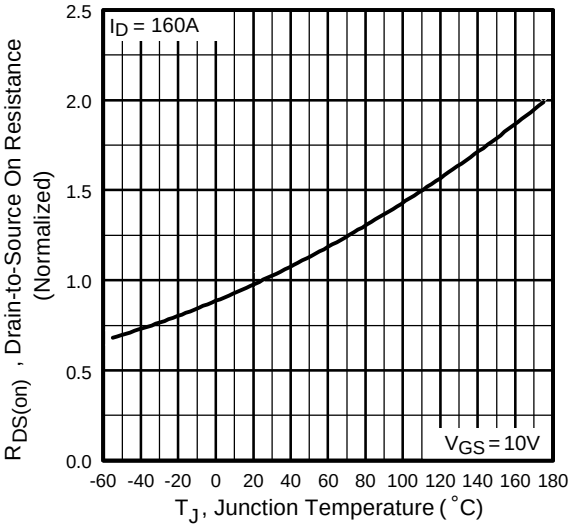

Fig 4. Normalized On-Resistance Vs. Temperature

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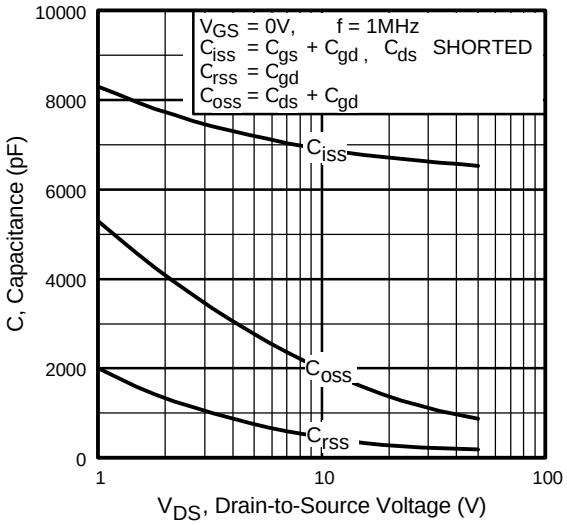

Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

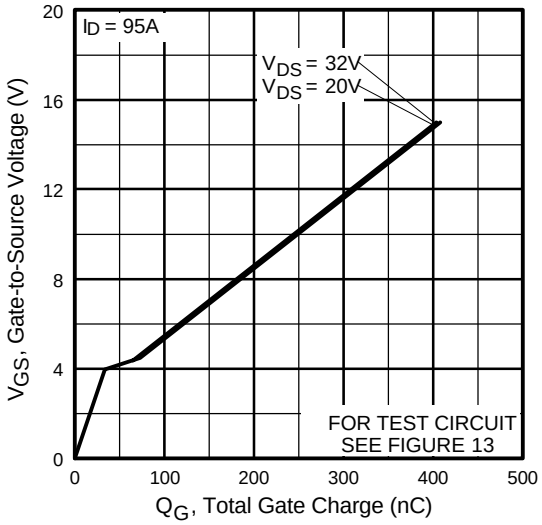

Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

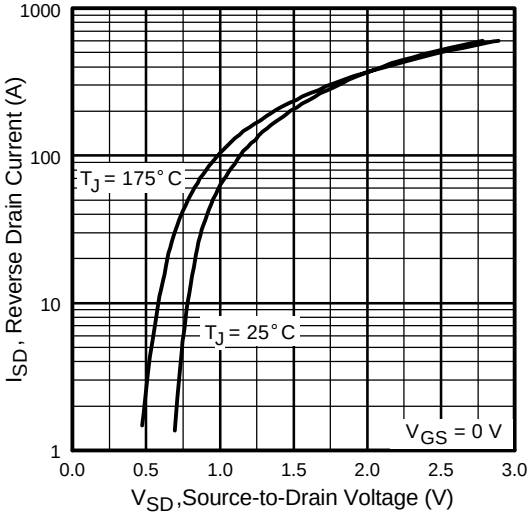

Fig 7. Typical Source-Drain Diode Forward Voltage

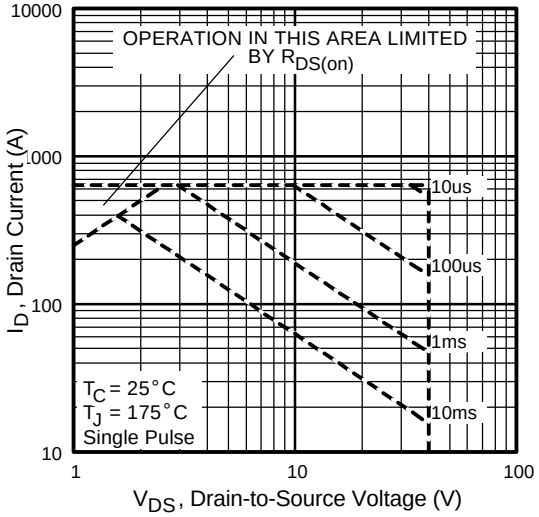

Fig 8. Maximum Safe Operating Area

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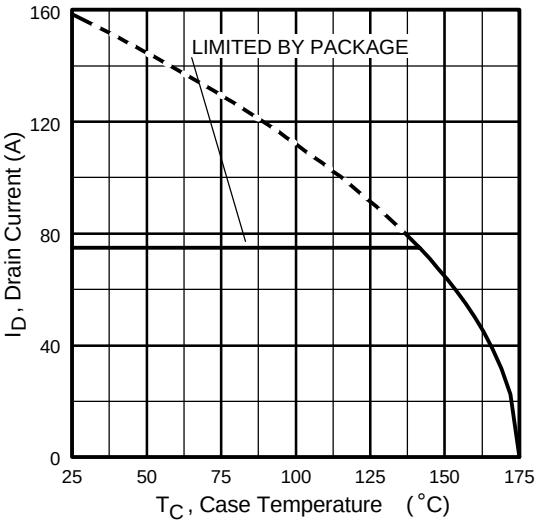
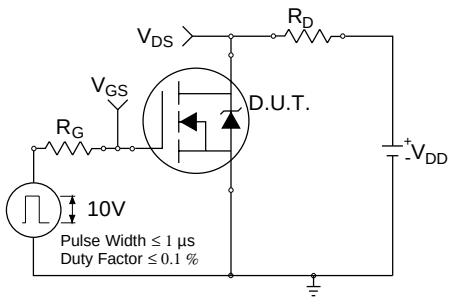
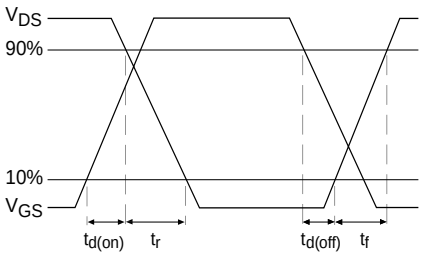


Fig 9. Maximum Drain Current Vs. Case Temperature





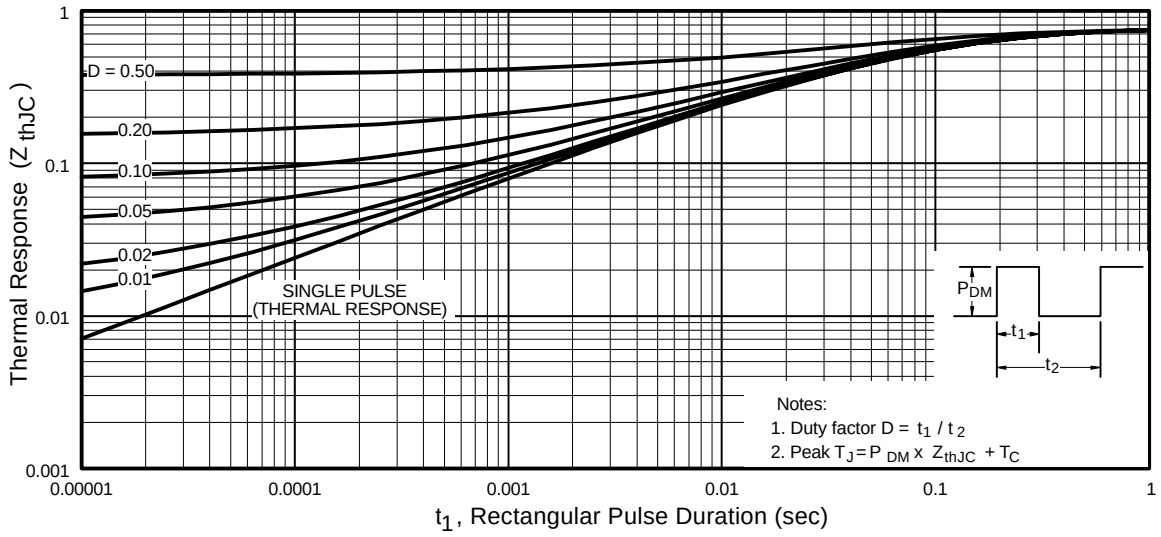


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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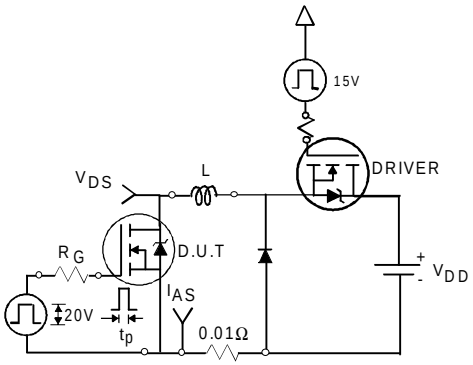

Fig 12a. Unclamped Inductive Test Circuit

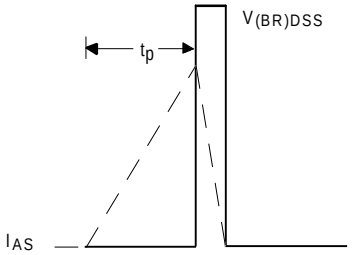

Fig 12b. Unclamped Inductive Waveforms

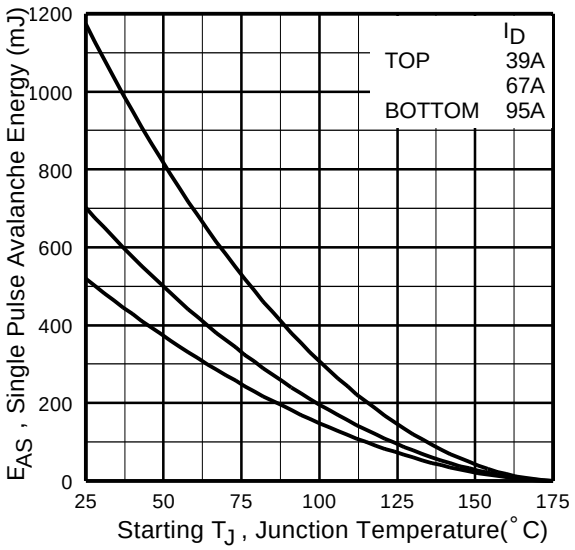

Fig 12c. Maximum Avalanche Energy Vs. Drain Current

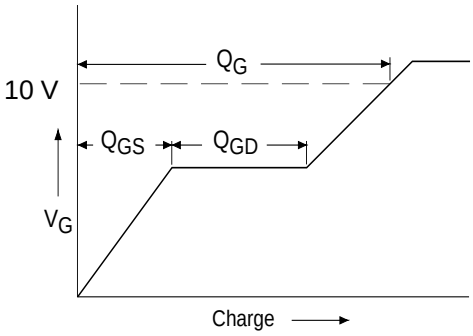

Fig 13a. Basic Gate Charge Waveform

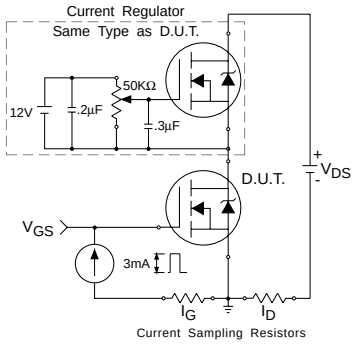

Fig 13b. Gate Charge Test Circuit

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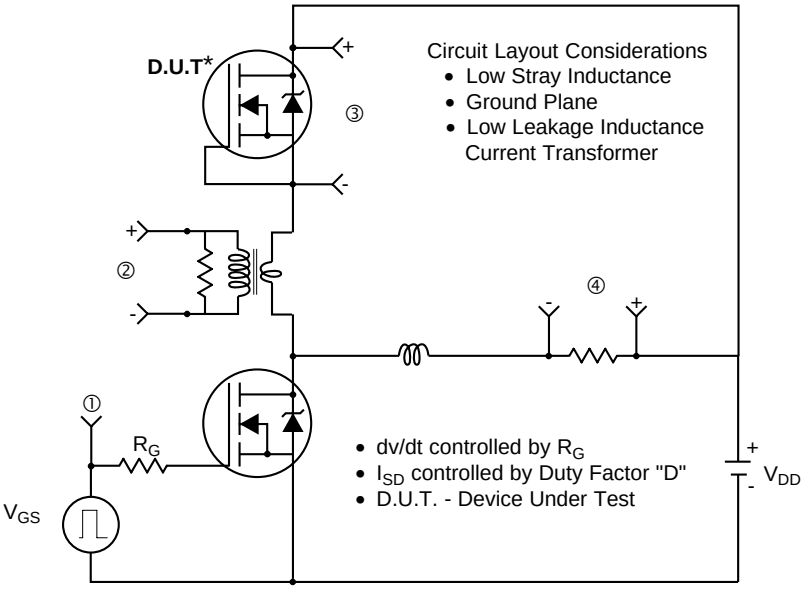
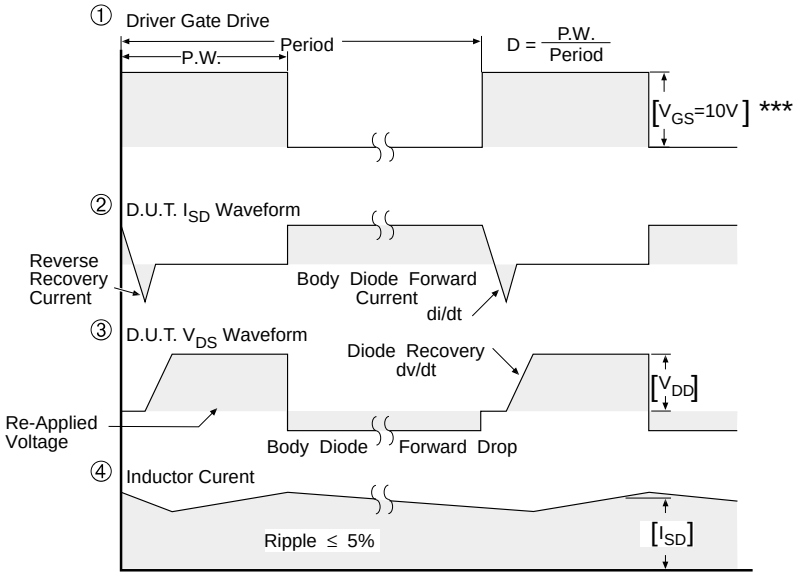
Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 14. For N-channel HEXFET® power MOSFETs

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)

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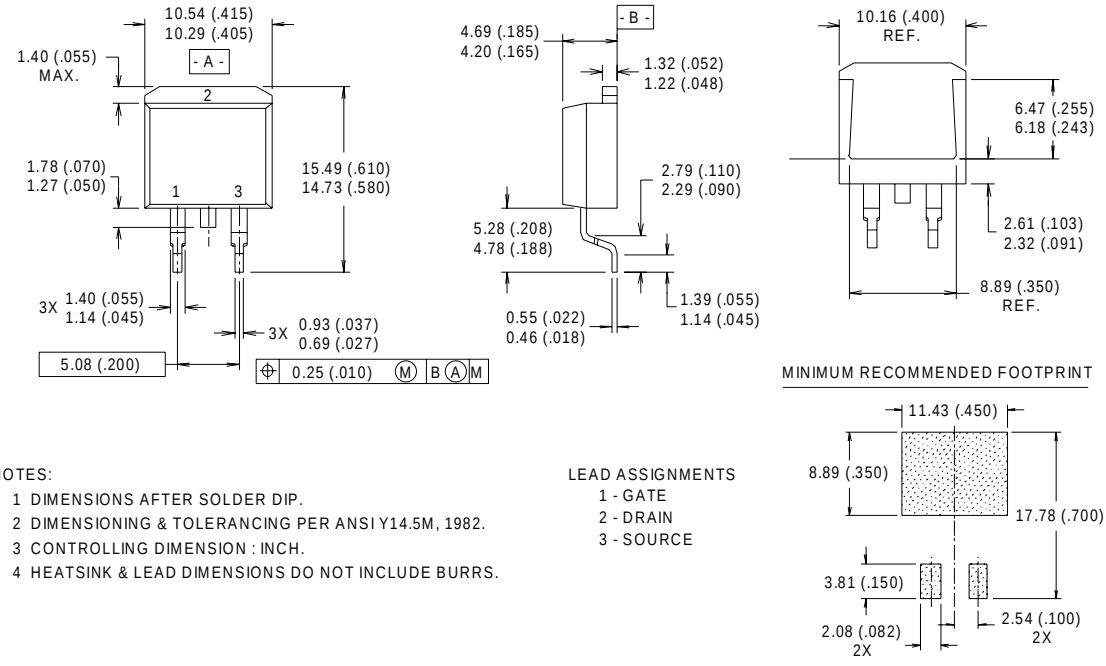


NOTES:

1 DIMENSIONS AFTER SOLDER DIP.
2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
3 CONTROLLING DIMENSION : INCH.
4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

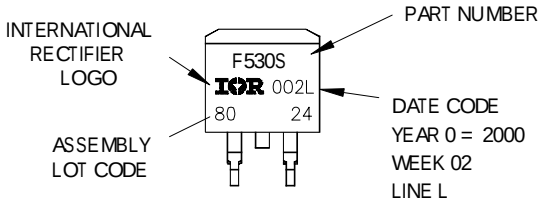
LEAD ASSIGNMENTS

1 - GATE
2 - DRAIN
3 - SOURCE

MINIMUM RECOMMENDED FOOTPRINT

D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"



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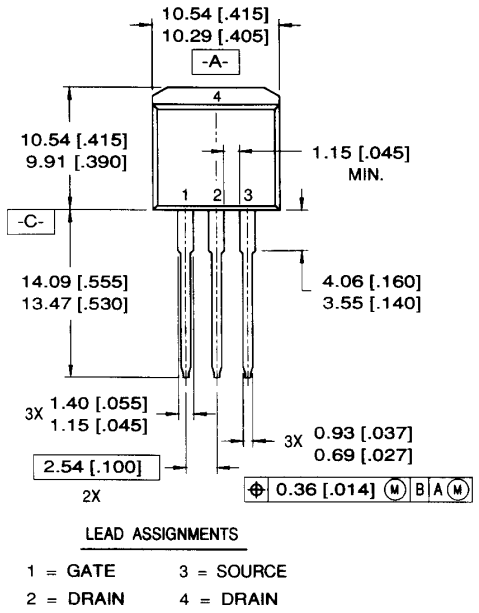
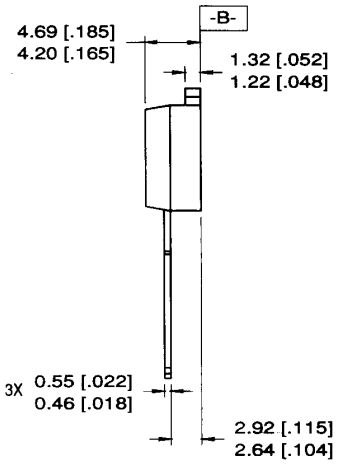
TO-262 Package Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS

1 = GATE 3 = SOURCE
2 = DRAIN 4 = DRAIN

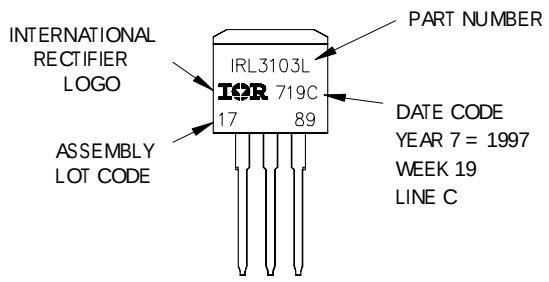


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



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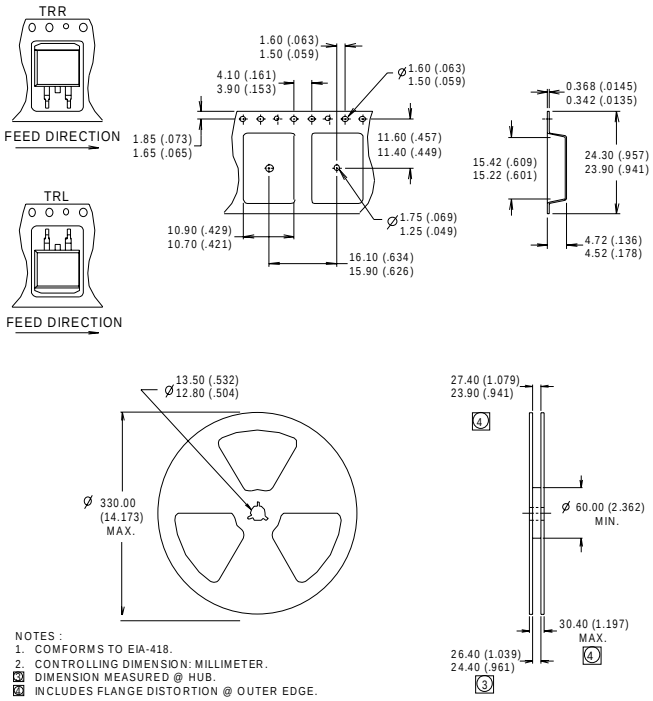
D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 0.35mH R_G = 25Ω, I_{AS} = 95A. (See Figure 12)

③ $I_{SD} \leq$ 95A, di/dt ≤ 160A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑥ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handing of the package refer to Design Tip # 93-4.

⑦ This is applied to D²Pak, When mounted on 1" square PCB (FR-4 or G-10 Material) . For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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